

# **AAP Review - Electron Source**

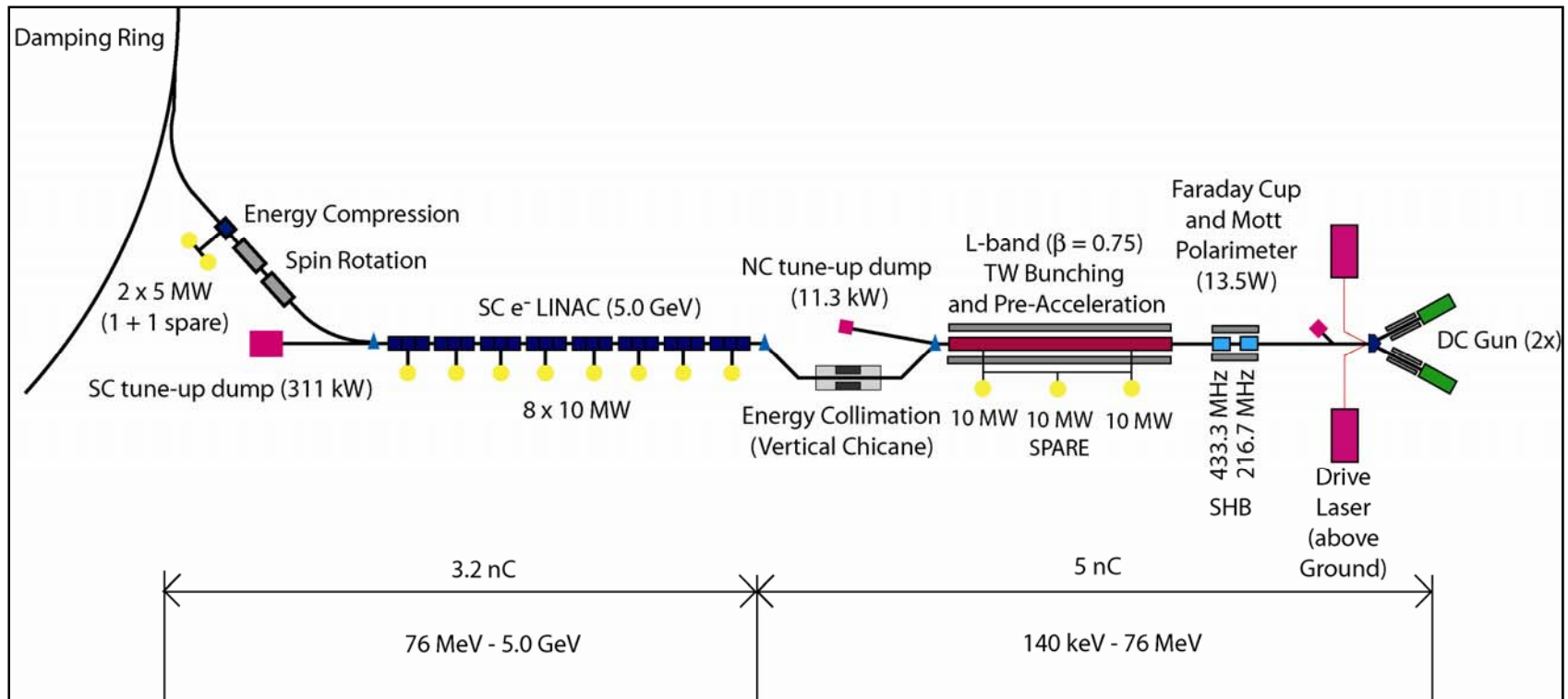
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SLAC**

**AAP Review Meeting, Tsukuba, April 2009**



# The Baseline Source

Electron source provides polarized electron beam and consists of all systems from source laser to 5 GeV injection to damping rings.



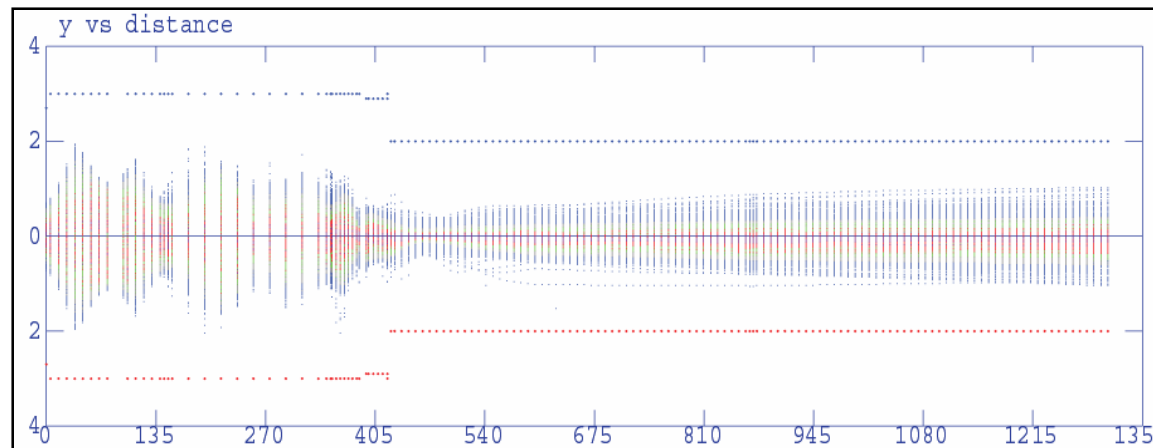


# Source Parameters

Parameter	Symbol	Value	Unit
Electrons per bunch (at gun exit)	$n_e$	$3 \times 10^{10}$	Number
Electrons per bunch (at DR injection)	$n_e$	$2 \times 10^{10}$	Number
Number of bunches	$N_e$	~ 3000	Number
Bunch repetition rate	$F_{\mu b}$	3	MHz
Bunch train repetition rate	$F_{mb}$	5	Hz
Bunch length at source	$\Delta t$	~ 1	ns
Current in bunch at source	$I_{avg}$	3.2	A
Energy stability	S	< 5	% rms
Polarization	$P_e$	80 (min)	%
Photocathode quantum efficiency	QE	0.5	%
Drive laser wavelength	$\lambda$	$790 \pm 20$	nm
Single bunch laser energy	E	5	$\mu J$

- Complete set of optics from Gun to DR is available
- Low Energy simulations : include space charge

## Example: Beam envelope along the NC injector



- 95% of electrons produce by the DC gun are captured within 6-D damping ring acceptance:

$$\gamma(A_x + A_y) \leq 0.09 \text{ m} \text{ and } \Delta E \times \Delta z \leq (\pm 25 \text{ MeV}) \times (\pm 3.46 \text{ cm})$$

- Source Laser System
  - This is primarily an engineering task
  - Challenge is to integrate various state of the art laser technology aspects into one system that is matched to Photocathode and Gun
- DC Gun
  - High Voltage/High Gradient to counteract space charge forces
  - UHV technology ( $10^{-12}$  Torr)
- Photocathodes
  - Main issue is the surface charge limit
  - QE/Polarization



# R&D Program

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Active R&D focus on 'critical' issues and accelerator physics:

– **SLAC:**

- Laser system development
- Photocathode R&D
- Optics design

– **Jlab**

- DC Gun development

– **Japan**

- Anticipate continuation of Univ. of Nagoya Photocathode and DC gun work at KEK

– **SBIR (DOE sponsored Industry collaboration)**

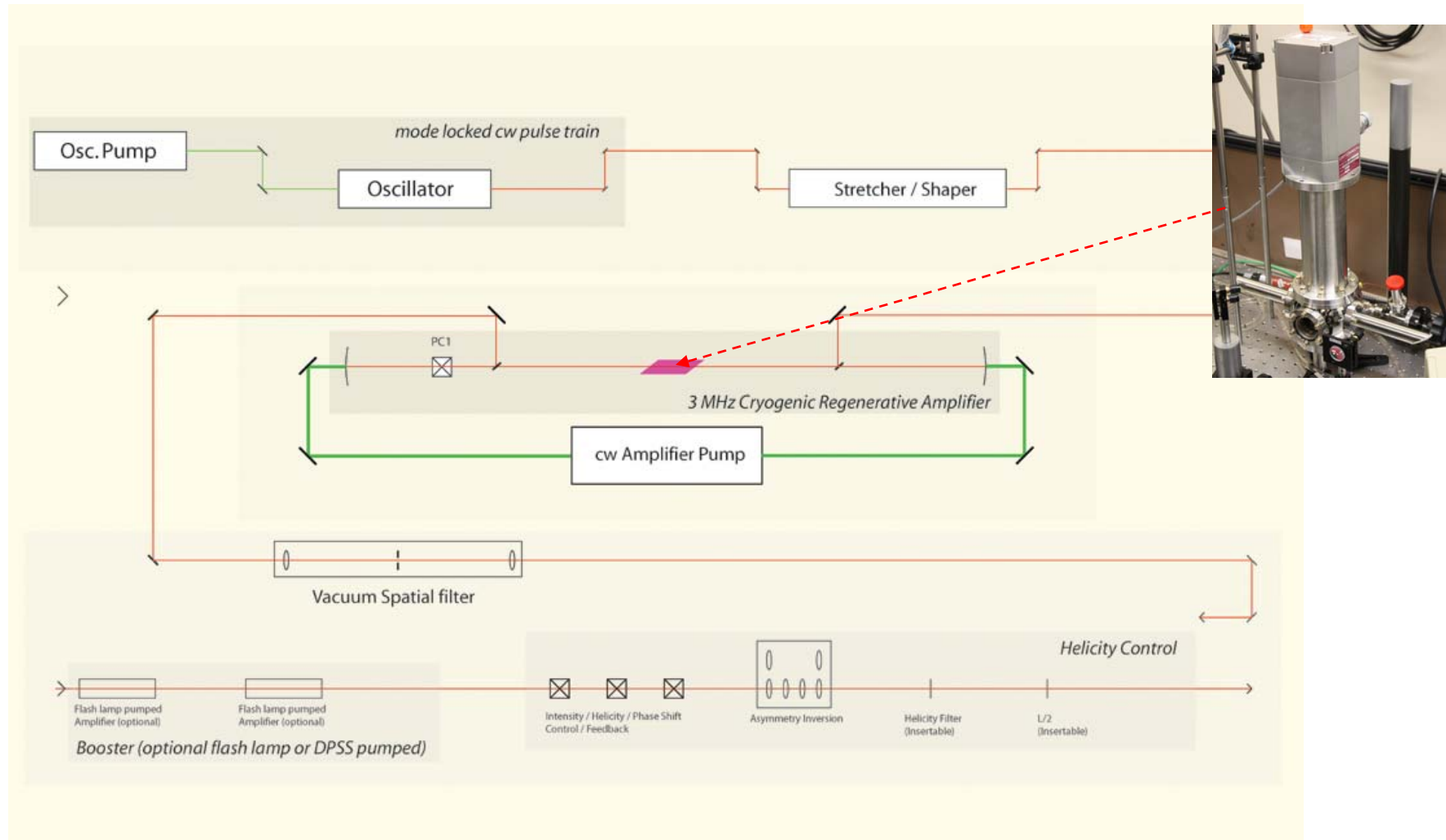
- Laser and photocathode R&D



# R&D beyond Baseline Design

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- RF guns for polarized beams
  - BNL: SC RF Gun
  - FNAL: NC RF Gun Plain Wave Transformer
- Source development at test facilities
  - E.g. STF @ KEK (but unpolarized)
- New method of generating polarized electrons from GaAs without NEA requirement
  - See talk by H. Tomizawa (Spring 8)



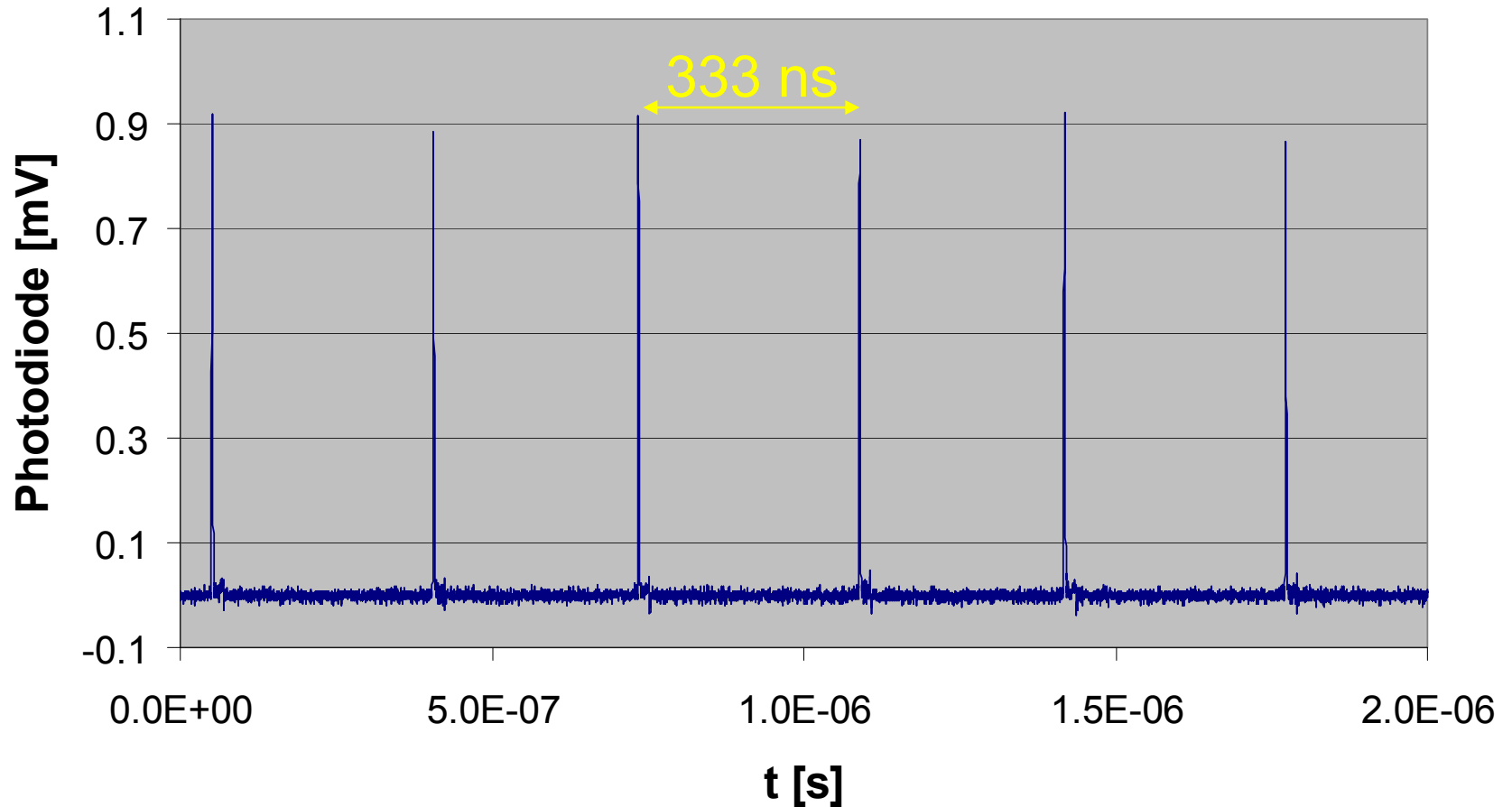


- Development of amplifier seed ✓
  - **Modelocked oscillator**
  - **Optical pulse stretching to 600 ps – 1 ns**
  
- Successful test of pulse switching at 3 MHz ✓
  - **component of regenerative amplifier**
  
- Current work now
  - **40 W frequency doubled cw Yb:YAG laser**
  - **Re-engineering of amplifier pump laser**
  
- For regenerative amplifier a cryogenically cooled Ti:Sapphire crystal will be used next
  - **Suppression of thermal lensing**

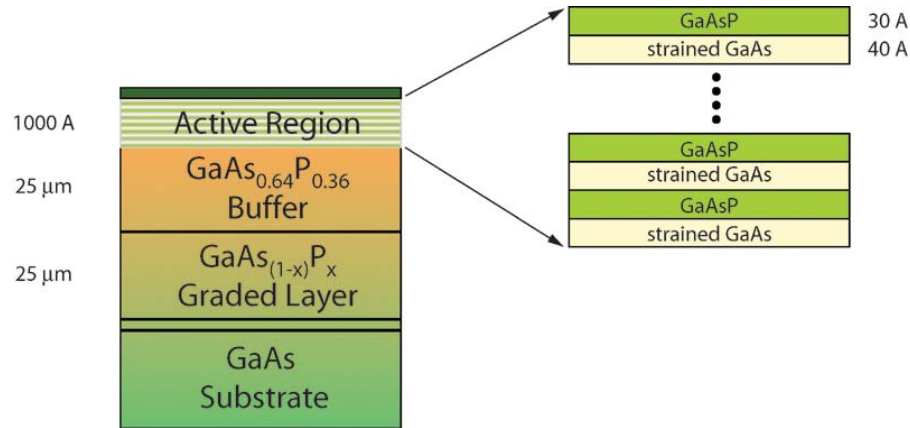


# Generation of 3 MHz seed pulse train

Switching of 79 MHz modelocked seed laser with 3 MHz Pockels cell:



## Baseline Design: GaAs/GaAsP



- Semiconductor engineering to optimize current designs to ILC conditions:
    - Composition and layer structure
    - Doping level
    - Activation technique
- } – QE
- } – Polarization
- } – Lifetime
- } – Surface charge limit

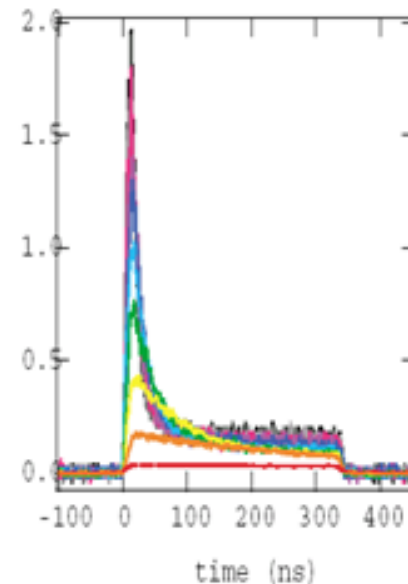
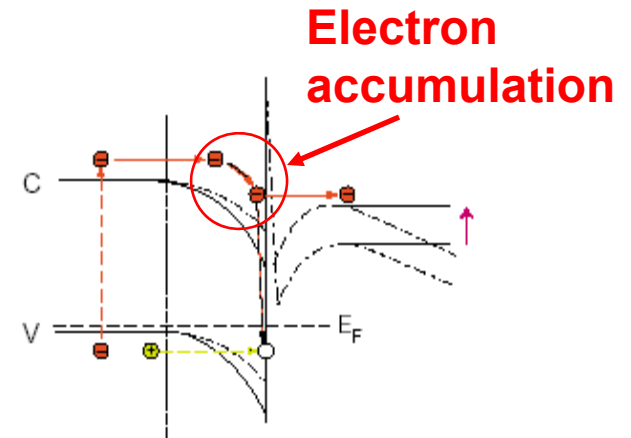


# Photocathode R&D Highlights

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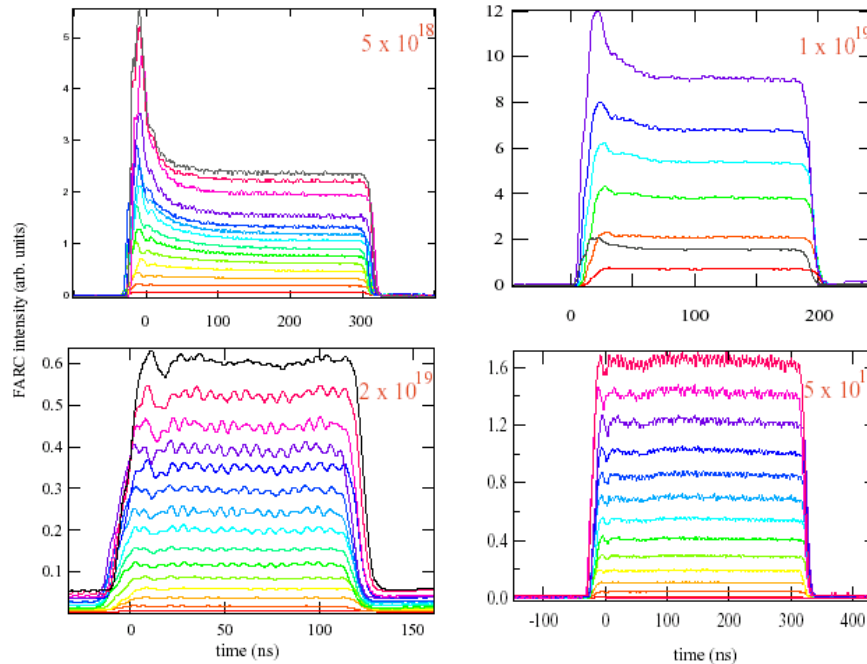
- Use of SLAC's polarized source development facility
- Faraday Rotation System to study depolarization mechanism
- Testing of various alternatives to GaAs/GaAsP → InAlGaAs, AlGaAs
- Co-deposition of alkali elements enhances cathode lifetime, improves robustness
  - **traditionally Cs only; new techniques e.g. Cs+Li**
    - SBIR/SLAC collaboration (SBIR partner: SAXET Surface Science, Inc)
- Most important question remains:
  - **Surface charge limit**
  - **needs ILC laser system**

- Photon absorption excites electrons to conduction band
- Electrons can be trapped near the surface; electron escape prob. < 20%
- Electrostatic potential from trapped electrons raises affinity
- Affinity recovers after electron recombination
- Increasing photon flux counterproductive at extremes



Optimization:  
Caveat:

Adjustment of doping level  
Negative effect on Polarization



Four samples with different doping levels:  
 $5 \times 10^{18} \text{ cm}^{-3}$   
 $1 \times 10^{19} \text{ cm}^{-3}$   
 $2 \times 10^{19} \text{ cm}^{-3}$   
 $5 \times 10^{19} \text{ cm}^{-3}$

~ 2 A (laser limited)

ILC peak current  
at source: 4 to 5 A

Measurement at ms time scale is required!

- Based on past experience at SLAC and Jlab
- Currently Gun R&D program is carried out at Jlab under Matt Poelkers leadership
- Synergy with CEBAF injector development
  - **Beneficial to ILC**
- R&D program:
  - **UHV technology (vacuum system, materials)**
  - **HV design (power supply, normal vs. inverted)**
  - **Geometry of Pierce electrodes optimization for ILC beam**



- Minimum Machine does not change e- source parameters → fundamental design changes are unlikely
- Single tunnel design is feasible in general
- Questions :
  - Tunnel space sharing (multiple beam lines) needs CAD model and evaluation :
    - International working group for 3D visualization
  - RF distribution :
    - adopt main linac solution for SC part of the source



- RDR design remains baseline
  - Activities focus on R&D to solve critical source issues:
    - **Source Laser system**
    - **DC Gun for polarized beams**
    - **Photocathodes**
  - Goal is to demonstrate nominal ILC beam using optimized photocathodes, laser system and DC Gun
- integrated injector test lab